

AMENDMENT TO THE CLAIMS

Please accept amended claims 2, 18, 24 and 26 as follows:

1. (Previously presented) A method of selectively removing a metal layer in a process for fabricating a semiconductor device, comprising:

removing the metal layer with a cleaning solution, the cleaning solution comprising an acid solution and an oxidation agent containing iodine, wherein the oxidation agent containing iodine includes at least one selected from the group consisting of NH_4IO_3 , LiIO_3 , CaIO_3 , BaIO_3 , KI , and NH_4I wherein the cleaning solution further includes water.

2. (Currently amended) The method of claim 1, wherein the metal layer [[comprise]] comprises at least one of a titanium layer and a cobalt layer.

Claim 3 (canceled)

4. (Previously presented) The method of claim 1, wherein the acid solution includes at least one of sulfuric acid and phosphoric acid.

5. (Previously presented) The method of claim 1, wherein the cleaning solution includes water in an amount of about 30 wt% and less, and the oxidation agent containing iodine in an amount of about 0.003 to 10wt%.

6. (Previously presented) The method of claim 2, wherein the titanium layer comprises at least one of titanium nitride and titanium.

Claims 7-10 (canceled)

11. (Original) A method of selectively removing a metal layer in a process for forming a silicide layer comprising:

forming a silicon pattern over a substrate;
forming a metal layer over the substrate;
performing a silicide thermal treatment to form a metal silicide layer from silicidation reaction between the silicon and the metal layer;
cleaning a non-reacting metal layer that does not participate in the silicidation reaction using a cleaning solution,
wherein the cleaning solution includes an acid solution and an oxidation agent containing iodine.

12. (Original) The method of claim 11, wherein the metal layer includes at least one of cobalt, titanium, and nickel.

13. (Original) The method of claim 11, wherein the cleaning solution further includes water.

14. (Original) The method of claim 11, wherein the acid solution includes sulfuric acid and phosphoric acid, and the oxidation agent containing iodine includes at least one selected from the group consisting of KIO_3 , NH_4IO_3 , LiIO_3 , CaIO_3 , BaIO_3 , KI , and NH_4I .

15. (Original) The method of claim 14, wherein the cleaning solution includes water in an amount of about 30 wt% and less, and the oxidation containing iodine in an amount of about 0.003 to about 10wt%.

16. (Original) The method of claim 11, wherein the cleaning is performed at a temperature range of about room temperature to about 120°C.

17. (Original) The method of claim 11, further comprising a step of:
sequentially performing a first treatment using a mixture of NH_4OH and H_2O_2 and a second treatment using HF or sequentially performing a first treatment using a mixture gas of CF_4 and O_2 and a second treatment using HF before forming the metal

layer, so as to remove a natural oxide layer and to cure damage to the substrate.

18. (Currently amended) The method of claim 11, wherein the silicide thermal treatment comprises:

- performing a first thermal treatment;
- performing a first cleaning that removes [[a]] the non-reacting metal layer using the cleaning solution; and
- performing a second thermal treatment.

19. (Original) The method of claim 18, wherein the cleaning solution includes water in an amount of about 30 wt% and less, and the oxidation containing iodine in an amount of about 0.003 to about 10wt%.

20. (Original) The method of claim 19, wherein the acid solution includes at least one of sulfuric acid and phosphoric acid, and the oxidation agent containing iodine includes at least one selected from the group consisting of KIO_3 , NH_4IO_3 , LiIO_3 , CaIO_3 , BaIO_3 , KI , and NH_4I .

21. (Original) The method of claim 19, wherein the first cleaning is performed at a temperature range of about room temperature to about 120°C.

22. (Original) The method of claim 11, wherein the substrate further includes a tungsten layer, and the cleaning solution does not remove the tungsten layer.

23. (Original) The method of claim 11, further comprising:
forming a titanium nitride layer over the metal layer, after forming the metal layer and before performing the silicide thermal treatment,
wherein the cleaning solution removes the titanium nitride layer.

24. (Currently amended) The method of claim 23, wherein the silicide thermal treatment comprises;

performing a first thermal treatment;
performing a first cleaning that removes the titanium nitride layer and the non-reacting metal layer using the cleaning solution;
forming a second titanium nitride layer; and
performing a second thermal treatment,
wherein the cleaning solution removes the further formed titanium nitride layer and the non-reacting [[silicon]] metal layer.

25. (Original) A method of selectively removing a metal layer in a process for forming a silicide layer comprising:

forming a transistor comprising source/drain regions and a gate electrode over a silicon substrate;

forming a metal layer over the substrate;

forming a titanium nitride layer over the metal layer;

performing a thermal treatment to form a metal silicide layer from reaction between the silicon of the source/drain regions and the metal layer that directly contact the silicon ; and

performing a cleaning that removes the titanium nitride layer and a non-reacting metal layer that does not directly contact the silicon of the source/drain regions, using a cleaning solution,

wherein the cleaning solution includes an acid solution, an oxidation agent containing iodine and water.

26. (Currently amended) The method of claim 25, wherein the step of forming the transistor comprises:

forming a gate insulation layer, a polysilicon layer, a tungsten layer and a capping insulation layer over the silicon substrate;

forming a photoresist pattern over the capping [[nitride]] insulation layer;

forming the gate electrode by successively etching the layers formed thereunder using the photoresist pattern as a mask;

removing the photoresist pattern;

performing an ion implantation process to form the source/drain regions in the silicon substrate at both sides of the gate electrode ; and

forming nitride spacers on sidewalls of the gate electrode.

27. (Original) The method of claim 26, wherein the photoresist pattern is removed using the cleaning solution.

28. (Original) The method of claim 25, wherein the acid solution includes at least one of sulfuric acid and phosphoric acid, and the oxidation agent containing iodine includes at least one selected from the group consisting of KIO_3 , NH_4IO_3 , LiIO_3 , CaIO_3 , BaIO_3 , KI , and NH_4I , and the cleaning solution includes water in an amount of about 30 wt% and less and an oxidation agent containing iodine in an amount of about 0.003-about 10wt%.

29. (Original) The method of claim 28, wherein the cleaning is performed at a temperature range of about room temperature to about 120°C.

30. (Original) The method of claim 29, wherein the metal layer includes at least one of cobalt, titanium, and nickel.

31. (Original) The method of claim 25, wherein the step of forming the transistor comprises:

sequentially forming a gate insulation layer and a polysilicon layer over the silicon substrate;

forming a photoresist pattern over the polysilicon layer;

forming the gate electrode by successively etching the layers formed thereunder using the photoresist pattern as an etch mask;

removing the photoresist pattern;

performing an ion implantation process to form the source/drain regions in the silicon substrate at both sides of the gate electrode ; and

forming nitride spacers on sidewalls of the gate electrode,

wherein when the metal silicide layer is formed at the source/drain regions by performing the silicide thermal treatment, a metal silicide layer is formed on the polysilicon at an upper part of the gate electrode.

32. (Original) The method of claim 31, wherein the photoresist pattern is removed using the cleaning solution.

33. (Original) The method of claim 31, wherein the acid solution includes at least one of sulfuric acid and phosphoric acid, and the oxidation agent containing iodine includes at least one selected from the group consisting of KIO_3 , NH_4IO_3 , LiIO_3 , CaIO_3 , BaIO_3 , KI , and NH_4I , and the cleaning solution includes water in an amount of about 30 wt% and less and an oxidation agent containing iodine in an amount of about 0.003-about 10wt%.

34. (Original) The method of claim 33, wherein the cleaning is performed at a temperature range of about room temperature to about 120°C .

Claims 35-39 (canceled)

40. (Previously presented) The method of claim 11, wherein the oxidation agent containing iodine includes at least one selected from the group consisting of NH_4IO_3 , LiIO_3 , CaIO_3 , BaIO_3 , KI , and NH_4I , and the cleaning solution further includes water.